ma-N 2400 series Resist

ma-N 2400 is a negative tone electron beam resist with low resolution and high dry-etching resistance

Characteristics:

- Negative tone
- Electron-beam and DUV sensitive
- Low resolution
- Good thermal stability of the resist patterns
- High dry and wet etch resistance
- Easy to remove
- Not sensitive to white light

Resist available at TNFC	ma-N 2405, ma-N 2410
Storage	18-25 ºC. Do not refrigerate!
Surface Preparation	Oxygen plasma cleaning and dehydration bake for 2min @180°C are recommended. HMDS for Si and SiO_2 substrates.
Spin	Speed 1000-5000 rpm, 30 sec. (450-800 nm for 2405, 800-1700 nm for 2410)
Pre-bake	90°C hotplate, 2.5 min.
Expose	Dose 200-400 $\mu C/cm^2$ at 100 kV.
Develop	ma-D 525, 2-4 min
Rinse	DI water, 5 min
Dry	By dry N_2
Post-Bake	If required, the etch resistance and the thermal stability of the resist can be further increased. Post-bake of the developed resist patterns is suggested in an oven at 100°C for approximately 5-15 min.
Descum	Oxygen plasma asher
Stripping	Acetone, oxygen plasma

Link to ma-N 2400 series manufacturer's data sheet:

https://kayakuam.com//wp-content/uploads/2019/10/PI_ma-N2400.pdf

http://tnfc.utoronto.ca/wp-content/uploads/2016/09/ma-N-2400.pdf